

NPN-SWITCHING SILICON TRANSISTOR

Qualified per MIL-PRF-19500/251

DEVICES

2N2218	2N2219
2N2218A	2N2219A
2N2218AL	2N2219AL

LEVELS

JAN
JANTX
JANTXV
JANS *

* Also available in Radiation Hardened versions. See datasheet for JANSR2N2218 & JANSR2N2219

ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

Parameters / Test Conditions	Symbol	2N2218 2N2219	2N221A; L 2N2219A; L	Unit
Collector-Emitter Voltage	V_{CEO}	30	50	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current	I_C	800		mA
Total Power Dissipation @ $T_A = +25^\circ\text{C}$ @ $T_C = +25^\circ\text{C}$	P_T	0.8 3.0		W W
Operating & Storage Junction Temp. Range	T_{op}, T_{stg}	-55 to +200		$^\circ\text{C}$

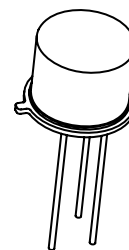
THERMAL CHARACTERISTICS

Parameters / Test Conditions	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	59	$^\circ\text{C/W}$

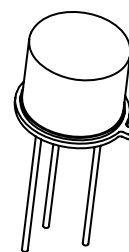
Note: (1) Derate linearly 4.6mW/ $^\circ\text{C}$ above $T_A > +25^\circ\text{C}$
(2) Derate linearly 17.0mW/ $^\circ\text{C}$ above $T_C > +25^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $I_E = 10\text{mA}$ 2N2218; 2N2219 2N2218A; 2N2219A / AL	$V_{(BR)CEO}$	30 50		Vdc
Emitter-Base Cutoff Current $V_{EB} = 5.0\text{Vdc}$ $V_{EB} = 6.0\text{Vdc}$ $V_{EB} = 4.0\text{Vdc}$ 2N2218; 2N2219 2N2218A; 2N2219A / AL All Types	I_{EBO}		10 10 10	μAdc ηAdc
Collector-Base Cutoff Current $V_{CE} = 30\text{Vdc}$ $V_{CE} = 50\text{Vdc}$ 2N2218; 2N2219 2N2218A; 2N2219A / AL	I_{CES}		10 10	ηAdc



TO-39 (TO-205AD)
2N2218, 2N2218A
2N2219, 2N2219A



TO-5
2N2218AL
2N2219AL

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted) (Con't)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit	
Collector-Base Cutoff Current V _{CB} = 50Vdc V _{CB} = 60Vdc V _{CB} = 60Vdc V _{CB} = 75Vdc	I _{CBO}		10 10 10 10	ηAdc μAdc ηAdc μAdc	
ON CHARACTERTICS (3)					
Forward-Current Transfer Ratio I _C = 0.1mAdc, V _{CE} = 10Vdc I _C = 1.0mAdc, V _{CE} = 10Vdc I _C = 10mAdc, V _{CE} = 10Vdc I _C = 150mAdc, V _{CE} = 10Vdc I _C = 500mAdc, V _{CE} = 10Vdc		h _{FE}	20 35 30 50 25 50 35 75 35 75 40 100 40 100 20 30	150 325 150 325	
Collector-Emitter Saturation Voltage I _C = 150mAdc, I _B = 15mAdc I _C = 500mAdc, I _B = 50mAdc			V _{CE(sat)}		0.4 0.3 1.6 1.0
Base-Emitter Saturation Voltage I _C = 150mAdc, I _B = 15mAdc I _C = 500mAdc, I _B = 50mAdc	V _{BE(sat)}			0.6 0.6	1.3 1.2 2.6 2.0

DYNAMIC CHARACTERISTICS

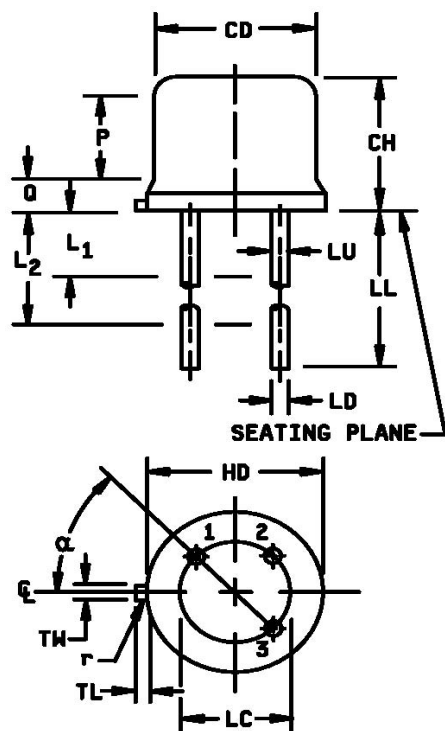
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of Small-Signal Forward Current Transfer Ratio $I_C = 20\text{mA}$, $V_{CE} = 20\text{V}$, $f = 100\text{MHz}$	$ h_{fe} $	2.5	12	
Small-Signal Forward Current Transfer Ratio $I_C = 1.0\text{mA}$, $V_{CE} = 10\text{V}$, $f = 1.0\text{kHz}$ 2N2218 2N2219 2N2218A, AL 2N2219A, AL	h_{fe}	25 50 35 75		
Output Capacitance $V_{CB} = 10\text{V}$, $I_E = 0$, $100\text{kHz} \leq f \leq 1.0\text{MHz}$	C_{obo}		8.0	pF
Input Capacitance $V_{EB} = 0.5\text{V}$, $I_C = 0$, $100\text{kHz} \leq f \leq 1.0\text{MHz}$	C_{ibo}		25	pF

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
$V_{CC} = 30\text{V}$; $I_C = 150\text{mA}$; $I_{B1} = 15\text{mA}$				
Turn-On Time (See Figure 3 of MIL-PRF-19500/251) 2N2218, 2N2219 2N2218A, 2N2219A / AL	t_{on}		40 35	μs
Turn-Off Time (See Figure 4 of MIL-PRF-19500/251) 2N2218, 2N2219 2N2218A, 2N2219A / AL	t_{off}		250 300	μs

(3) Pulse Test: Pulse Width = $300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

PACKAGE DIMENSIONS



	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		7
LD	.016	.019	0.41	0.48	8, 9
LL	See note 14				
LU	.016	.019	0.41	0.48	8, 9
L ₁		.050		1.27	8, 9
L ₂	.250		6.35		8, 9
P	.100		2.54		7
Q		.030		0.76	5
TL	.029	.045	0.74	1.14	3, 4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45° TP		45° TP		7

NOTES:

- Dimensions are in inches.
- Millimeters are given for general information only.
- Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- Dimension TL measured from maximum HD.
- Body contour optional within zone defined by HD, CD, and Q.
- CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
- All three leads.
- The collector shall be internally connected to the case.
- Dimension r (radius) applies to both inside corners of tab.
- In accordance with ASME Y14.5M, diameters are equivalent to øx symbology.
- Lead 1 = emitter, lead 2 = base, lead 3 = collector.
- For L suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For non-L suffix types (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.

FIGURE 1. Physical dimensions (similar to TO-39, TO-5).

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9